

/ Descriptions

WR0<5 ММ Ё SQS Æ Ñ ы s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

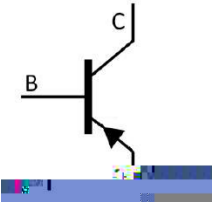
/ Features

Н ђ ϕ /э́ ll ђ ll ы ` /э́ М ђ я
Low noise, high DC current gain, high breakdown voltage.

/ Applications

ѼѼ Н ђ ϕ - l Ѽ Ѽ
Low noise audio amplifier applications.

/ Equivalent Circuit



/ Pinning



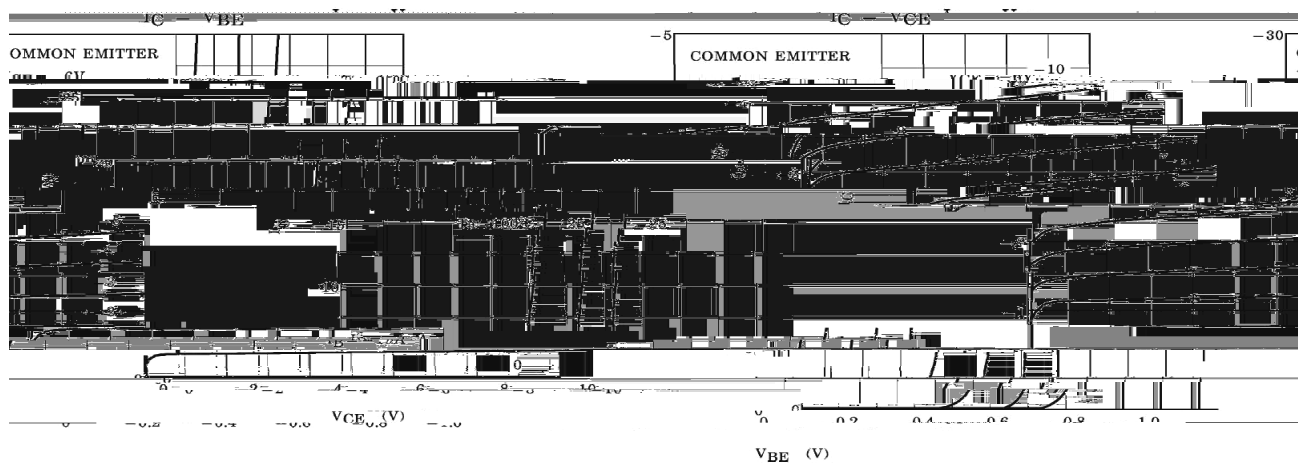
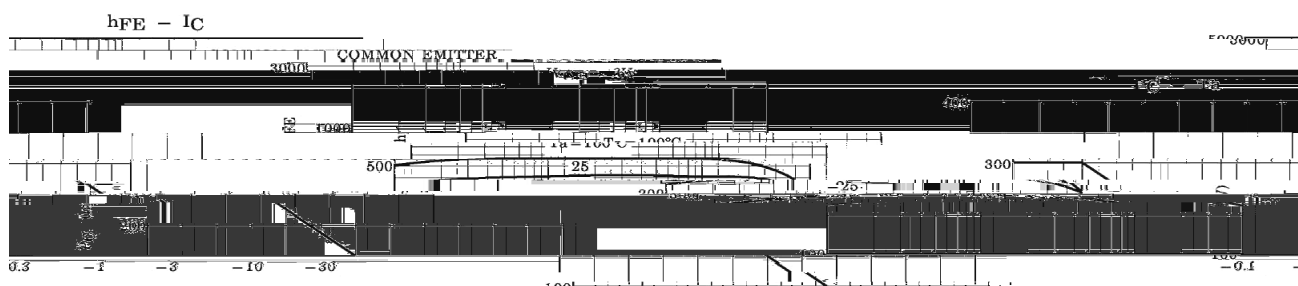
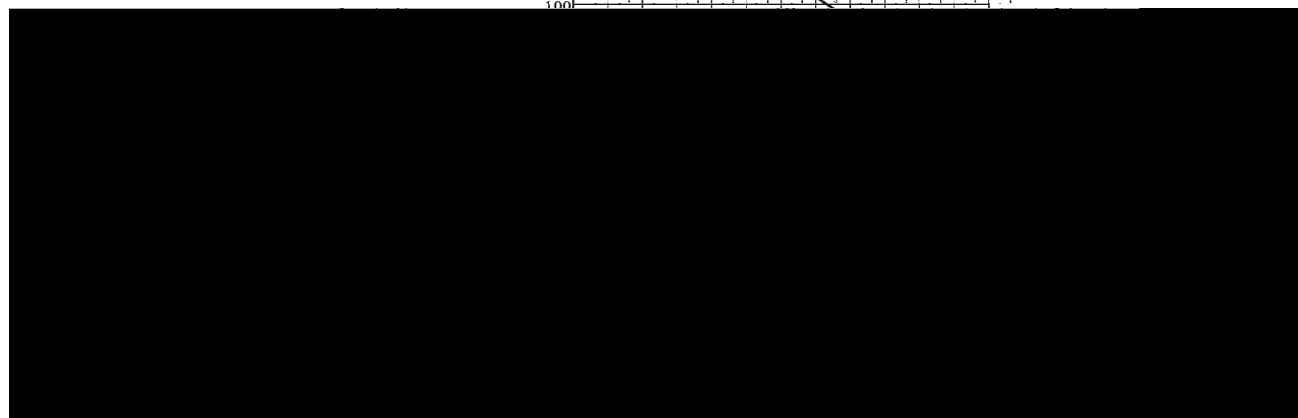
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ hFE Classifications & Marking

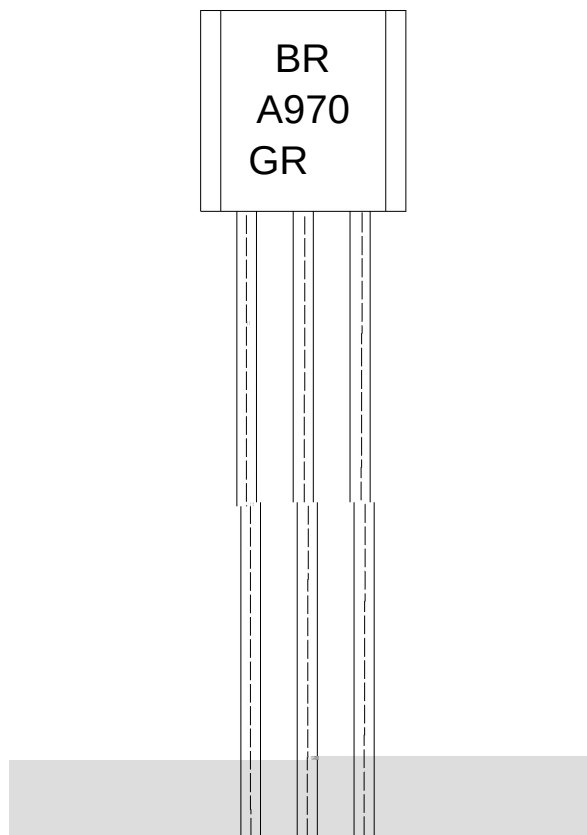
h _{FE} Classifications Symbol	GR	BL
h _{FE} Range	200~400	350~700

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current – Continuous	I_E	100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	152 591iw560.J/TT7 161 Tf28 TD0107	

/ Electrical Characteristic Curve



/ Marking Instructions



б " X

EU: ㄠ 3 ㄴ ㄱ

D<: 3 X ㄠ 3 ㄴ ㄱ

JU: ㄠ h_{FE} ' 6 ㄱ

---- X ㄠ 1 F ㄴ ㄴ ㄱ 1 ㄱ 1 F ㄴ ㄴ ㄱ

Note:

BR: Company Code.

A970: Product Type Code.

GR: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5 °C 0.5sec;
3. 3. Cooling Speed: 2~10 °C /sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5 °C 0.5sec.
3. Cooling Speed: 2~10 °C /sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” T Y E / BULK

Package Type	Units					Dimension		(unit mm3)

λ V γ ~ - t h Š ù